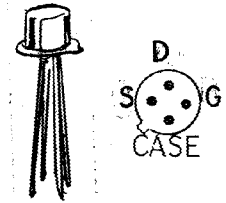


# MICRO ELECTRONICS MICRO

## 2N4416,A

N-CHANNEL FET

CASE TO-72



2N4416 and 2N4416A are N-channel field-effect transistors designed for general purpose amplifier and chopper applications.

### ABSOLUTE MAXIMUM RATINGS :

		2N4416	2N4416A
Drain-Gate Voltage	V <sub>DG</sub>	30V	35V
Drain-Source Voltage	V <sub>DS</sub>	30V	35V
Reverse Gate-Source Voltage	V <sub>GS</sub>	30V	35V
Gate Current	I <sub>G</sub>		10mA
Total Power Dissipation @ T <sub>A</sub> =25°C	P <sub>tot</sub>		300mW
Operating Junction & Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>		-65 to +200°C

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise specified)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Gate-Source Breakdown Voltage 2N4416 2N4416A	BV <sub>GSS</sub>	30 35		V	I <sub>G</sub> =1μA V <sub>DS</sub> =0
Gate-Source Forward Voltage	V <sub>GSF</sub>		1	V	I <sub>G</sub> =1mA V <sub>DS</sub> =0
Gate Reverse Current	I <sub>GSS</sub>		100 200	pA pA	V <sub>GS</sub> =20V V <sub>DS</sub> =0 V <sub>GS</sub> =20V V <sub>DS</sub> =0 T <sub>A</sub> =150°C
Gate-Source Cutoff Voltage 2N4416 2N4416A	V <sub>GS(off)</sub>	2.5	6 6	V	V <sub>DS</sub> =15V I <sub>D</sub> =1nA
Gate-Source Voltage	V <sub>GS</sub>	1	5.5	V	V <sub>DS</sub> =15V I <sub>D</sub> =0.5mA
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	5	15	mA	V <sub>DS</sub> =15V V <sub>GS</sub> =0
Small-Signal Common-Source Forward Transfer Admittance	Y <sub>fs</sub>	4.5	7.5	mmho	V <sub>DS</sub> =15V V <sub>GS</sub> =0 f=1KHz

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